

**PNP Silicon Switching Transistor**

- Low collector-emitter saturation voltage
- Complementary type:  
SMBT2222A / MMBT2222A (NPN)
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



Type	Marking	Pin Configuration			Package
SMBT2907A/MMBT2907A	s2F	1 = B	2 = E	3 = C	SOT23

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CEO}$	60	V
Collector-base voltage	$V_{CBO}$	60	
Emitter-base voltage	$V_{EBO}$	5	
Collector current	$I_C$	600	mA
Base current	$I_B$	100	
Peak base current	$I_{BM}$	200	
Total power dissipation $T_S \leq 77\text{ °C}$	$P_{tot}$	330	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-65 ... 150	

**Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>1)</sup>	$R_{thJS}$	$\leq 220$	K/W

<sup>1)</sup>For calculation of  $R_{thJA}$  please refer to Application Note AN077 (Thermal Resistance Calculation)

**Electrical Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC Characteristics</b>					
Collector-emitter breakdown voltage $I_C = 10\text{ mA}, I_B = 0$	$V_{(BR)CEO}$	60	-	-	V
Collector-base breakdown voltage $I_C = 10\text{ }\mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	60	-	-	
Emitter-base breakdown voltage $I_E = 10\text{ }\mu\text{A}, I_C = 0$	$V_{(BR)EBO}$	5	-	-	
Collector-base cutoff current $V_{CB} = 50\text{ V}, I_E = 0$ $V_{CB} = 50\text{ V}, I_E = 0, T_A = 150\text{ }^\circ\text{C}$	$I_{CBO}$	-	-	0.01 10	$\mu\text{A}$
Emitter-base cutoff current $V_{EB} = 5\text{ V}, I_C = 0$	$I_{EBO}$	-	-	10	nA
DC current gain <sup>1)</sup> $I_C = 100\text{ }\mu\text{A}, V_{CE} = 10\text{ V}$ $I_C = 1\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 10\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 150\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 500\text{ mA}, V_{CE} = 10\text{ V}$	$h_{FE}$	75 100 100 100 50	- - - - -	- - - 300 -	-
Collector-emitter saturation voltage <sup>1)</sup> $I_C = 150\text{ mA}, I_B = 15\text{ mA}$ $I_C = 500\text{ mA}, I_B = 50\text{ mA}$	$V_{CEsat}$	- -	- -	0.4 1.6	V
Base emitter saturation voltage <sup>-1)</sup> $I_C = 150\text{ mA}, I_B = 15\text{ mA}$ $I_C = 500\text{ mA}, I_B = 50\text{ mA}$	$V_{BEsat}$	- -	- -	1.3 2.6	

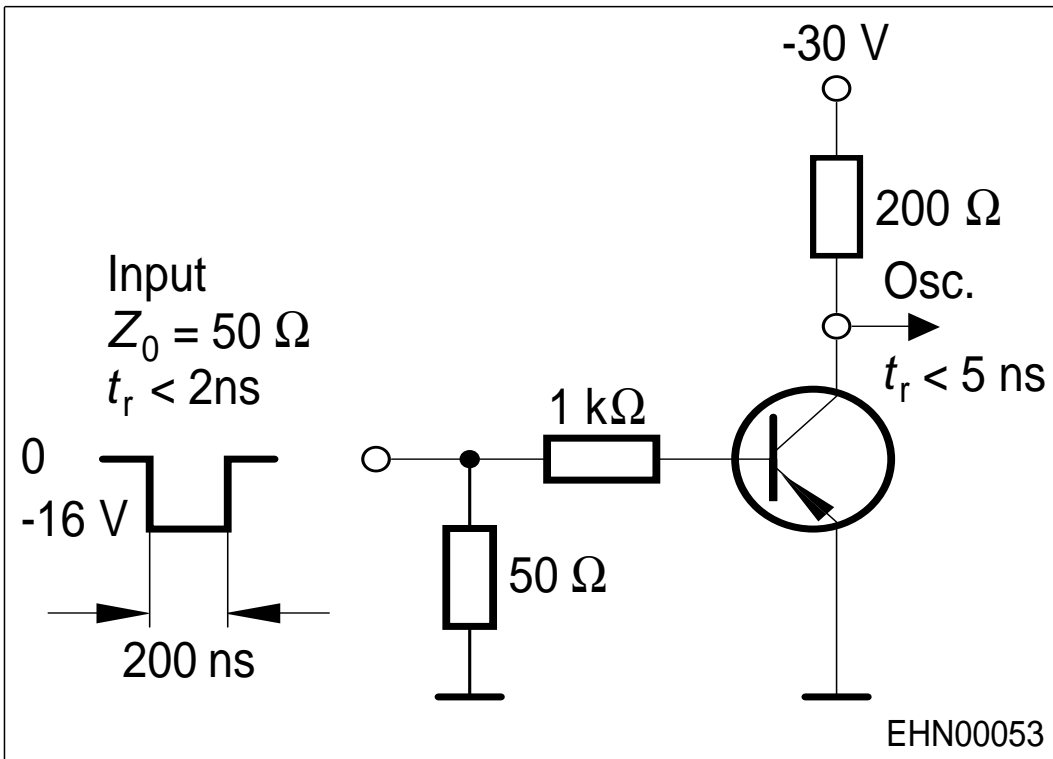
<sup>1</sup>Puls test:  $t \leq 300\mu\text{s}$ ,  $D = 2\%$

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

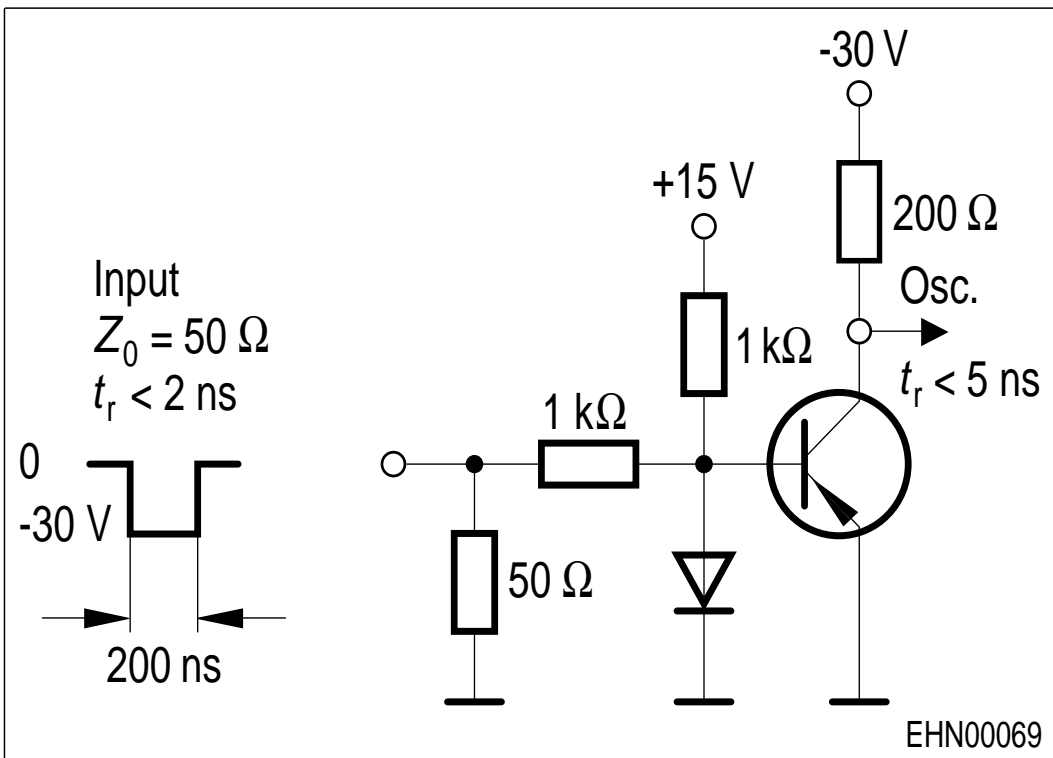
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>AC Characteristics</b>					
Transition frequency $I_C = 20\text{ mA}, V_{CE} = 20\text{ V}, f = 100\text{ MHz}$	$f_T$	200	-	-	MHz
Collector-base capacitance $V_{CB} = 10\text{ V}, f = 1\text{ MHz}$	$C_{cb}$	-	-	8	pF
Emitter-base capacitance $V_{EB} = 0.5\text{ V}, f = 1\text{ MHz}$	$C_{eb}$	-	-	30	
Delay time $V_{CC} = 30\text{ V}, I_C = 150\text{ mA}, I_{B1} = 15\text{ mA},$ $V_{BE(off)} = 0.5\text{ V}$	$t_d$	-	-	10	ns
Rise time $V_{CC} = 30\text{ V}, I_C = 150\text{ mA}, I_{B1} = 15\text{ mA},$ $V_{BE(off)} = 0.5\text{ V}$	$t_r$	-	-	40	
Storage time $V_{CC} = 30\text{ V}, I_C = 150\text{ mA}, I_{B1} = I_{B2} = 15\text{ mA}$	$t_{stg}$	-	-	80	
Fall time $V_{CC} = 30\text{ V}, I_C = 150\text{ mA}, I_{B1} = I_{B2} = 15\text{ mA}$	$t_f$	-	-	30	

Test circuit

Delay and rise time



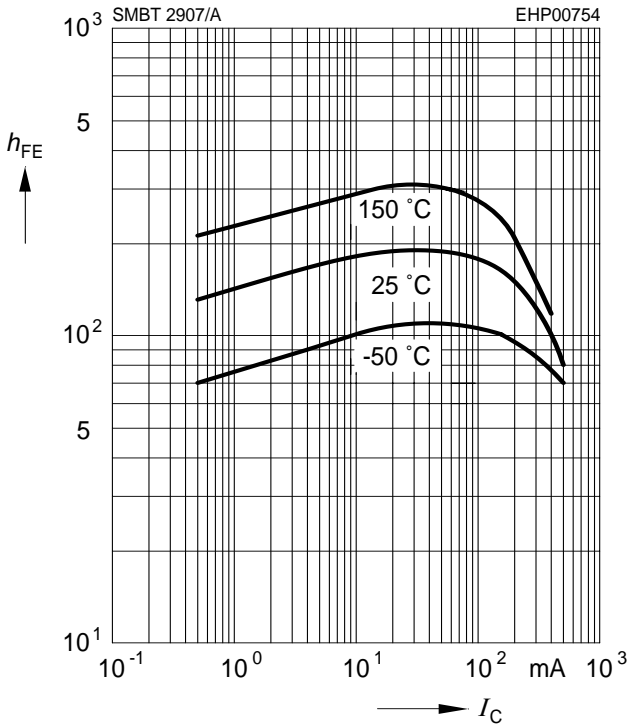
Storage and fall time



Oscilloscope:  $R > 100$ ,  $C < 12 \text{ pF}$ ,  $t_r < 5 \text{ ns}$

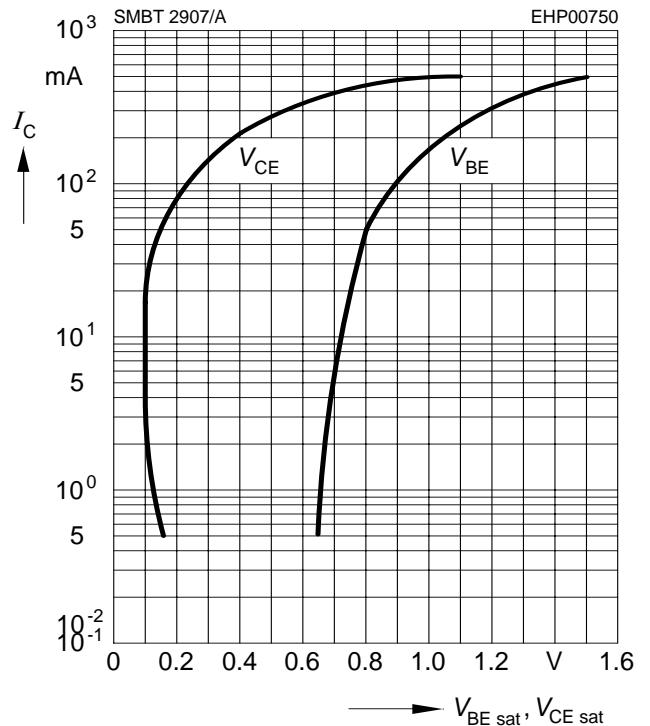
**DC current gain  $h_{FE} = f(I_C)$**

$V_{CE} = 5\text{ V}$



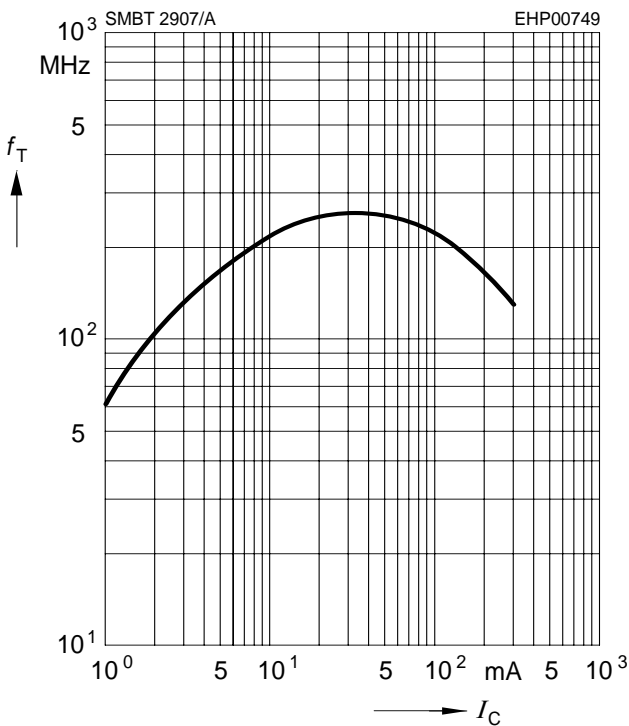
**Saturation voltage  $I_C = f(V_{BEsat}; V_{CEsat})$**

$h_{FE} = 10$



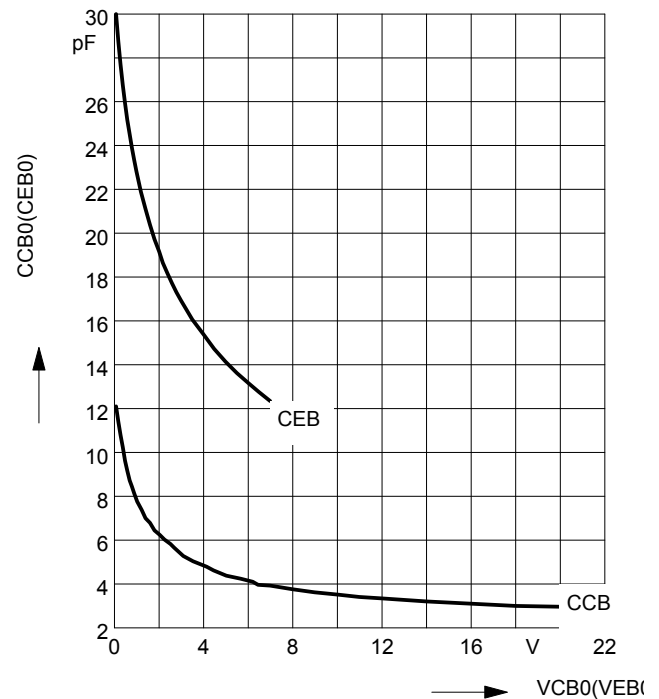
**Transition frequency  $f_T = f(I_C)$**

$V_{CE} = 5\text{ V}$



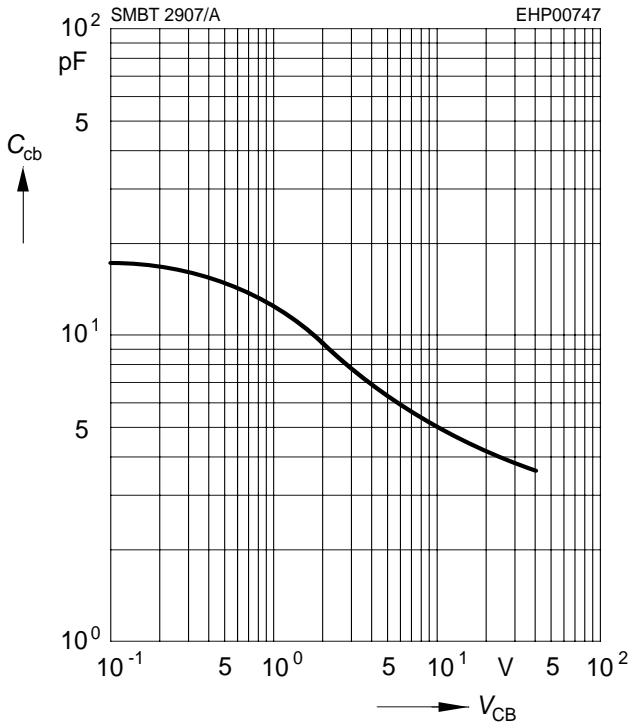
**Collector-base capacitance  $C_{cb} = f(V_{CB})$**

**Emitter-base capacitance  $C_{eb} = f(V_{EB})$**

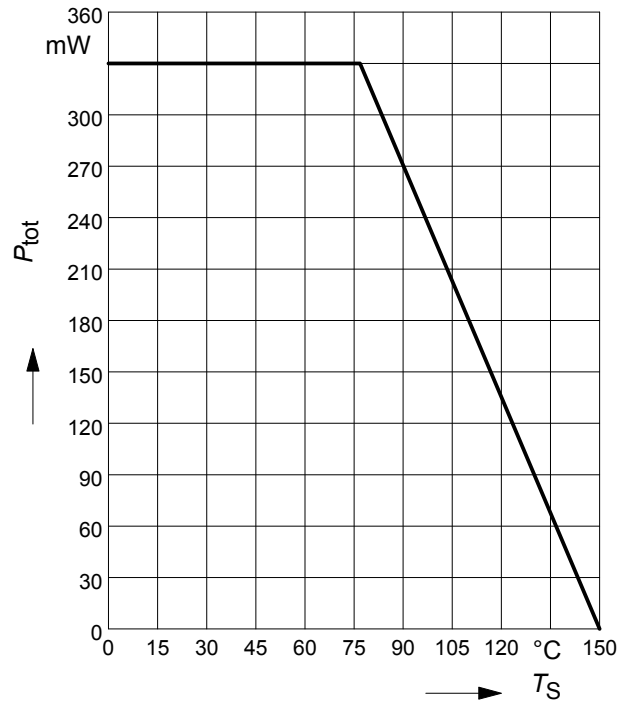


**Collector-base capacitance  $C_{CB} = f(V_{CB})$**

$f = 1\text{MHz}$

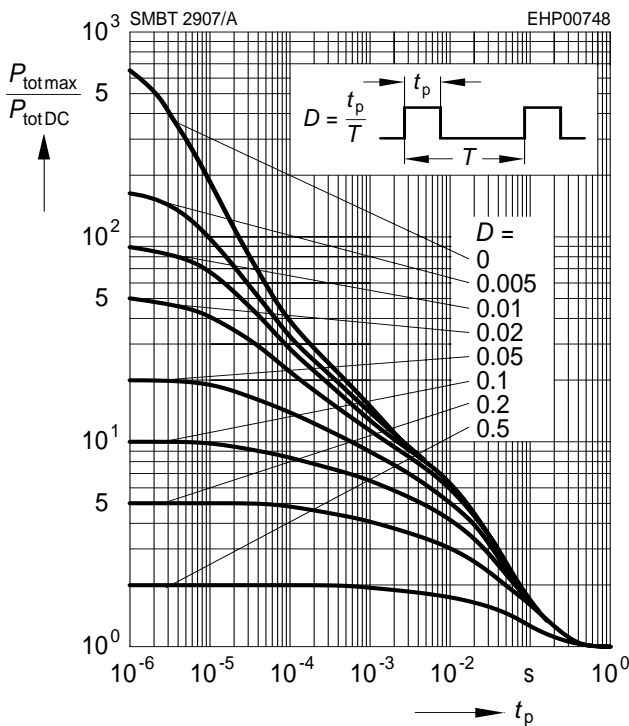


**Total power dissipation  $P_{tot} = f(T_S)$**



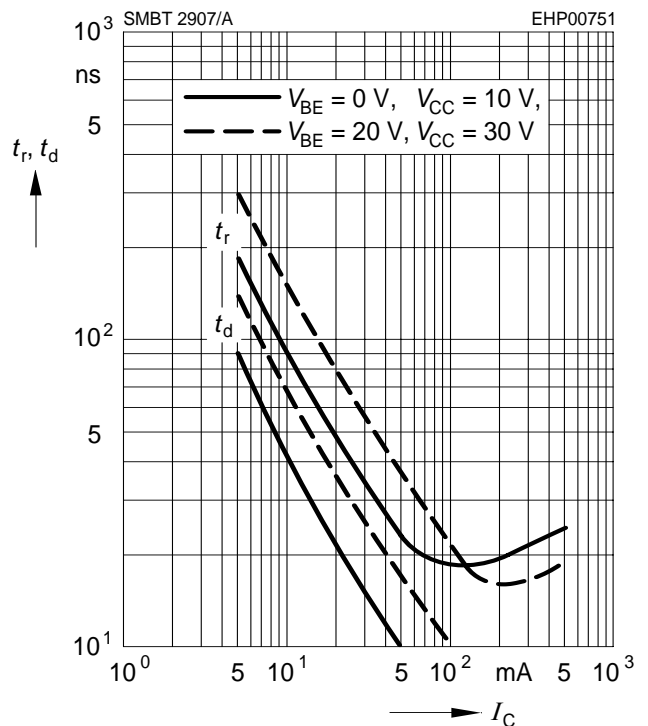
**Permissible Pulse Load**

$P_{totmax}/P_{totDC} = f(t_p)$



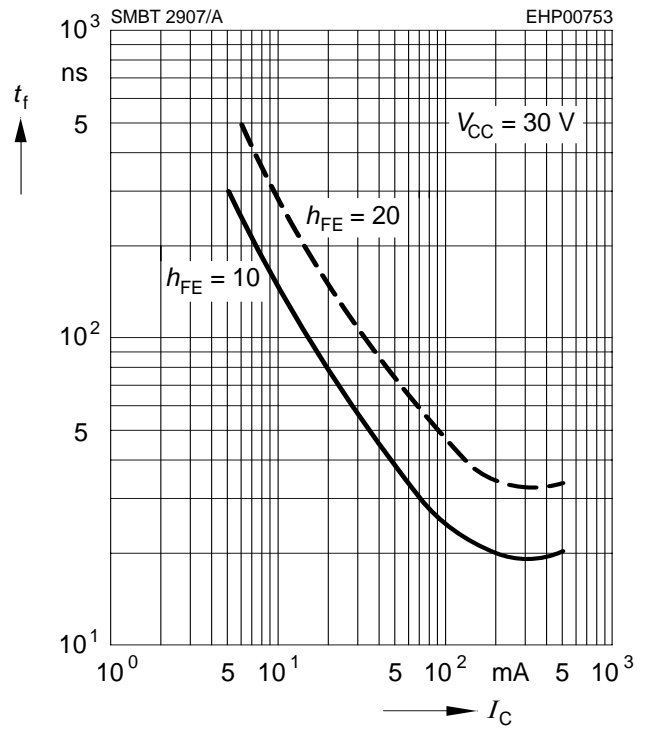
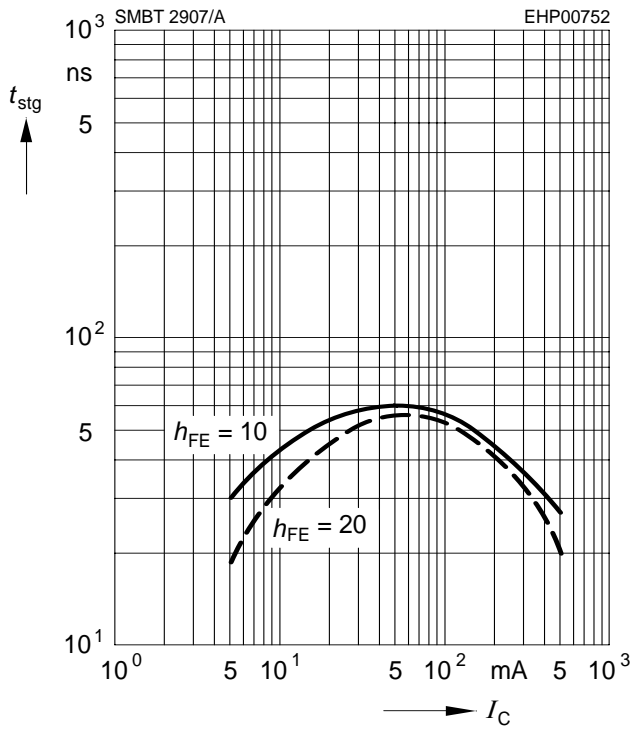
**Delay time  $t_d = f(I_C)$**

**Rise time  $t_r = f(I_C)$**



Storage time  $t_{stg} = f(I_C)$

Fall time  $t_f = f(I_C)$



Package Outline



1) Lead width can be 0.6 max. in dambar area

Foot Print



Marking Layout (Example)



Standard Packing

Reel  $\varnothing 180$  mm = 3.000 Pieces/Reel  
 Reel  $\varnothing 330$  mm = 10.000 Pieces/Reel





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